

DOCKET NO: 249248US2DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
MASAYOSHI HIRAO, ET AL. : ATTN: APPLICATION DIVISION
SERIAL NO: NEW APPLICATION :
FILED: HEREWITH :
FOR: SEMICONDUCTOR DEVICE WITH :
SEMICONDUCTOR CHIP FORMED BY :
USING WIDE GAP SEMICONDUCTOR :
AS BASE MATERIAL :

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 8 of this paper.